Abstract of the Disclosure (FIG. 1)

"PLASMA TREATMENT METHOD AND APPARATUS"

A plasma treatment method comprising exhausting a process chamber (2) so as to decompress the process chamber (2), mounting a wafer on a suscepter (5), supplying a process gas to the wafer through a shower electrode (21), applying high frequency power, which has a first frequency f_1 lower than an inherent lower ion transit frequencies of the process gas, to the suscepter (5), and applying high frequency power, which has a second frequency f_2 higher then an inherent upper ion transit frequencies of the process gas, whereby a plasma is generated in the process chamber (2) and activated species influence the wafer.

This Sheet Has Been Replaced

